

TO-92 Plastic-Encapsulate Transistors

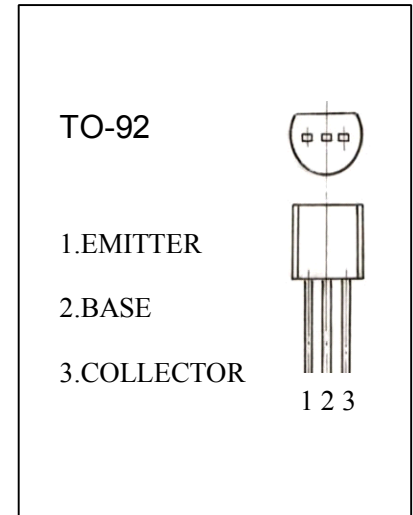
A94 TRANSISTOR (PNP)

FEATURES

High voltage

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-400	V
V _{CE0}	Collector-Emitter Voltage	-400	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _c	Collector Current -Continuous	-0.2	A
P _c	Collector Power Dissipation	0.625	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55 to +150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR) CBO}	I _c = -100μA, I _E =0	-400			V
Collector-emitter breakdown voltage	V _{(BR) CEO}	I _c = -1mA, I _B =0	-400			V
Emitter-base breakdown voltage	V _{(BR) EBO}	I _E =-100μA, I _c =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-400V, I _E =0			-0.1	μA
Collector cut-off current	I _{CE0}	V _{CE} =-400V, I _B =0			-5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _c =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _c =-10mA	80		300	
	h _{FE(2)}	V _{CE} =-10V, I _c =-1mA	70			
	h _{FE(3)}	V _{CE} =-10V, I _c =-100mA	60			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-10mA, I _B =-1mA			-0.2	V
	V _{CE(sat)}	I _c =-50mA, I _B =-5mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =-10mA, I _B = -1mA			-0.75	V
Transition frequency	f _t	V _{CE} =-20V, I _c =-10mA f =30MHz	50			MHz

Typical Characteristics

A94

